

FIG. 1

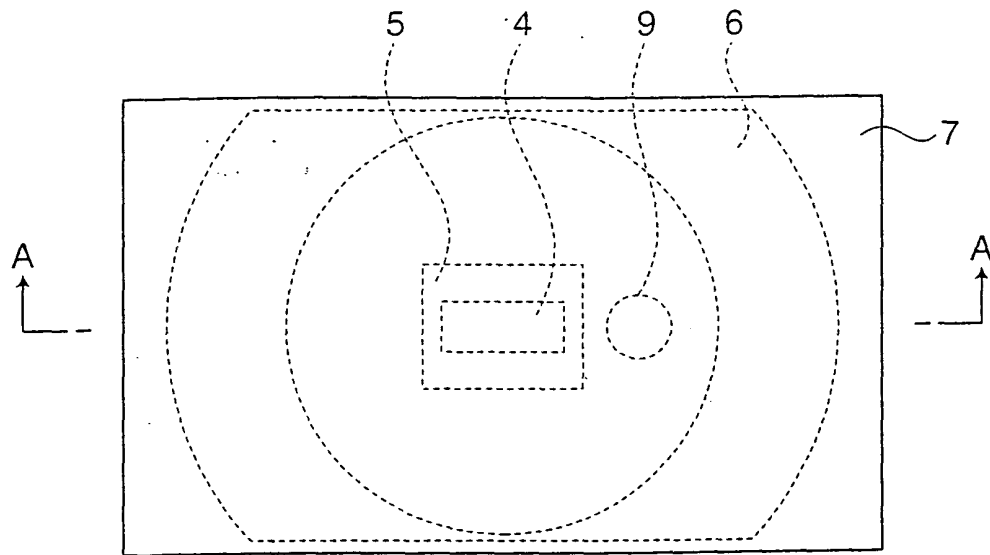
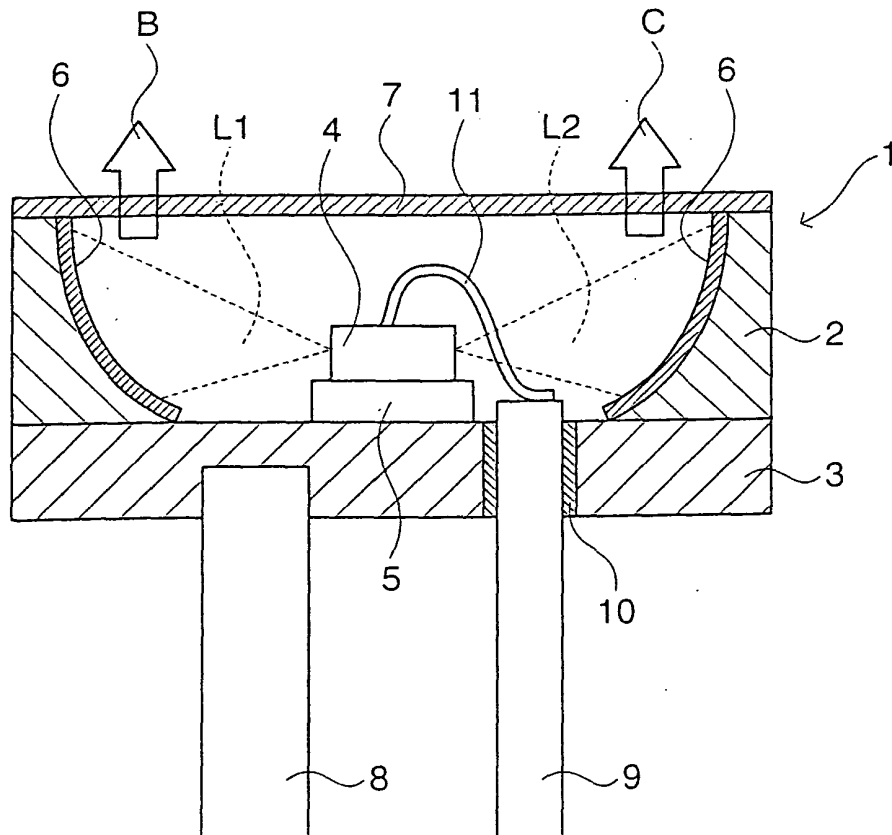


FIG. 2



[illegible]

A cross-sectional view of a semiconductor device 1a. The device consists of a substrate 2 with a top layer 3a and a bottom layer 3b. A central region 4 contains a stack of layers 5, 6, and 7. A curved layer 8 is on the left side, and a curved layer 9 is on the right side. A layer 11 is on top of the central region 4. Two upward arrows, labeled B and C, indicate light emission from the top surface. Dashed lines L1 and L2 represent light paths originating from the central region 4 and reflecting off the curved layers 8 and 9, respectively. Labels 8a and 9a point to the bottom surfaces of the curved layers 8 and 9, respectively.

Fig. 1a is a cross-sectional view of a semiconductor device. It shows a substrate 1a with a top layer 7 and a bottom layer 2. A central block 4 is connected to a base 5a via a wire 6a. A side contact 3a is connected to the base 5a via a wire 9a. Arrows indicate upward flow from the base 5a.

FIG. 7

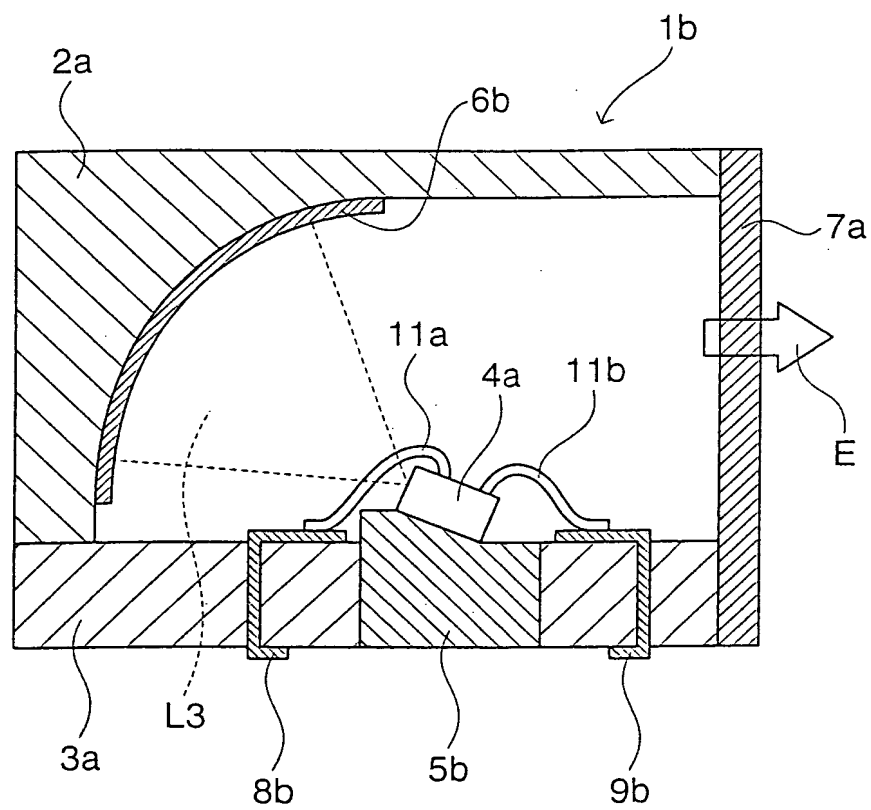


FIG. 8

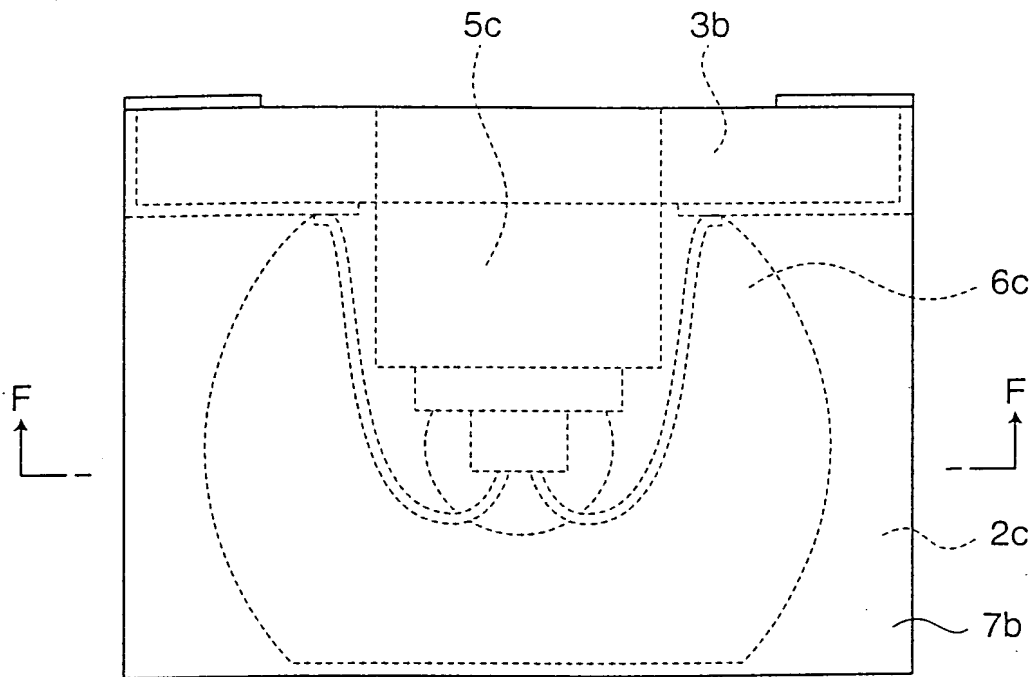


FIG. 9

